

Data Sheet

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Low Power, High Performance Radiation Hardened Operational Amplifier

HS-2700RH is radiation hardened internally compensated operational amplifiers which employ dielectric isolation to achieve excellent DC and dynamic performance with very low quiescent power consumption.

DC performance of the amplifier input is characterized by high CMRR (106dB), low offset voltage (0.5mV), along with low bias and offset current (5.0nA and 2.5nA respectively). These input specifications, in conjunction with offset null capability and open-loop gain of 300,000V/V, enable HS-2700RH to provide accurate, high-gain signal amplification. Gain bandwidth 1MHz and slew rate of 20V/ μ s allow for processing of fast, wideband signals. Input and output signal amplitudes of at least ±11V can be accommodated while providing output drive capability of 10mA. For maximum reliability, the output is protected in the event of short circuits to ground.

The amplifier operates from a wide range of supplies (\pm 5.5V to \pm 20V) with a maximum quiescent supply drain of only 150µA. HS-2700RH is therefore, ideally suited to low-power instrumentation and filtering applications that require fast, accurate response over a wide range of signal frequency.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed here must be used when ordering.

Detailed Electrical Specifications for these devices are contained in SMD 5962-95670. A "hot-link" is provided on our homepage for downloading. www.intersil.com/spacedefense/space.asp

Features

- Electrically Screened to SMD # 5962-95670
- QML Qualified per MIL-PRF-38535 Requirements

•	Low Power Supply Current	150μΑ (Max) 90μΑ (Typ)
•	High CMRR	86dB (Min) 106dB (Typ)
•	Low Input Bias Current	20nA (Min) 5nA (Typ)
•	Low Offset Current	10nA (Min) 2.5nA (Typ)
•	Total Dose1 x	10 ⁴ RAD(Si)

Applications

- High Gain Amplifier
- Instrumentation Amplifiers
- Active Filters
- Telemetry Systems
- Battery-Powered Equipment

Ordering Information

ORDERING NUMBER	INTERNAL MKT. NUMBER	TEMP. RANGE (^o C)
5962D9567002VCA	HS1-2700RH-Q	-55 to 125
5962D9567002VCC	HS1B-2700RH-Q	-55 to 125
5962D9567002VGA	HS2-2700RH-Q	-55 to 125

Pinouts



HS2-2700RH (CAN) MACY1-X8 TOP VIEW



Test Circuit





Timing Waveforms









FIGURE 3. TRANSIENT RESPONSE WAVEFORM

NOTE: Measured on both positive and negative transitions. Capacitance at Compensation pin should be minimized.

Typical Performance Curves $T_A = 25^{\circ}C$, VSUPPLY = ±15V, Unless Otherwise Specified















FIGURE 5. INPUT BIAS CURRENT AND OFFSET CURRENT AS A FUNCTION OF TEMPERATURE



FIGURE 7. BIAS CURRENT AS A FUNCTION OF DIFFERENTIAL INPUT VOLTAGE



FIGURE 9. POWER SUPPLY CURRENT AS A FUNCTION OF TEMPERATURE

Typical Performance Curves $T_A = 25^{\circ}C$, VSUPPLY = ±15V, Unless Otherwise Specified (Continued)



FIGURE 10. VOLTAGE GAIN AS A FUNCTION OF TEMPERATURE

NOTE: Open loop (comparator) applications are not recommended, because of the above characteristic.

Burn-In Circuits





NOTES:

- 1. R1 = 1M Ω , ±5%, 1/4W (Min)
- 2. C1 = C2 = 0.01 μ F/Socket (Min) or 0.1 μ F/Row (Min)
- 3. D1 = D2 = 1N4002 or equivalent (per board)
- 4. $|(V+) (V-)| = 31V \pm 1V$

HS2-2700RH METAL CAN



NOTES:

- 5. $R1 = 1M\Omega, \pm 5\%, 1/4W$ (Min)
- 6. $C1 = 0.01 \mu F/Socket$ (Min)
- 7. $C2 = C3 = 0.01 \mu F/Socket$ (Min) or $0.1 \mu F/Row$ (Min)
- 8. D1 = D2 = 1N4002 or equivalent (per board)
- 9. |(V+) (V-)| = 31V ±1V
- 10. Insulated scope probe must be used during board check-out.

HS-2700RH





Schematic Diagram



NOTE: Nominal currents shown in microamperes.

Die Characteristics

DIE DIMENSIONS:

70 mils x 60 mils x 20 mils (1780µm x 1530µm x 1530µm)

INTERFACE MATERIALS:

Glassivation:

Type: Nitride Thickness: 7kÅ ±0.7kÅ

Top Metallization:

Type: Aluminum Thickness: 16kÅ ±2kÅ

Substrate:

Linear Bipolar, DI

Backside Finish:

Silicon

Metallization Mask Layout

ASSEMBLY RELATED INFORMATION:

Substrate Potential (Powered Up): Unbiased

ADDITIONAL INFORMATION:

Worst Case Current Density: $< 2 \times 10^5 \text{ A/cm}^2$

<text>

HS-2700RH

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